

Abstract of the Disclosure

The present invention is related to a method for fabricating a capacitor capable of preventing a contact 5 between neighboring lower electrodes even if a height of the lower electrode increases. The lower electrode is formed to have a critical dimension wider at a bottom region than at a top region to thereby be firmly supported. Also, a wider distance between the lower electrodes prevents neighboring 10 lower electrodes from contacting to each other. As a result of these effects, it is possible to prevent a failure of dual bit, which eventually results in higher yields of semiconductor devices.